CRM Product Name Rule

CRM MOSFET Naming Rule(LV/MV MOSFET)

1	2	3	4	5	6	7	8
CRM	K	T	L	10	130	A	Q

8: Special Suffix
Blank= Single
D= Dual same Die
C= Dual different Die
M= Multi-die >2
Q= Automotive, DQ/CQ/MQ for Dual Die,Multi Die
A/B...Any other special use;

7. Parameters option(use to distinguish part name when two devices have same process,package, Vds and Rdson range)
A= First 1
B= Option 2
K= with ESD(First1), KB with ESD(Option2)...
F= with FRD(First1), FB with FRD(Option2)...
J= Unconventional Pin

6. CP Rds(on) Typ (mohm)
D9= 0.9mohm
02= 2mohm
10= 10mohm
100= 100mohm
1K5= 1.5ohm
1D7= 1.7mohm

5. Vdss - Max（BVDSS/10）
03= 30V VDS
10= 100V VDS
15= 150V VDS

4. Vth
V= (Logic level, Vth typ <0.6V)
U= Low Vth (Logic level, Vth typ 0.6~1V)
L= Low Vth (Logic level, Vth typ 1~2V)
H= High Vth(Vth typ >=2V)

3. Channel/Type
T= N channel Trench
B= P channel Trench
G= N channel SGT
E= P channel SGT

2. Package Code
K　　　TO-252-3L
L　　　SOT-23
G　　　PDFN5x6-8L / PDFN5x6-8L-D
Q　　　PDFN3.3x3.3-8L / PDFN3.3x3.3-8L-D
P　　　SOP-8
C　　　TO-220C-3L
E　　　TO-263-3L
J　　　SOT-23-3L

1. Prefix
CRM　　CRM MOSFET

CRM MOSFET Naming Rule(Super Junction)

1	2	3	4	5	6	7
CRM	K	C	80	R380	A	Q

7.Special Suffix
Default= Blank
Q= Automotive

6. Parameters option(use to distinguish part name when two devices have same process,package, Vds and Rdson range)

A= First 1
B= Option 2
K= with ESD(First1), KB with ESD(Option2)…
F= with FRD(First1), FB with FRD(Option2)…

5. CP Rds(on) Max (mohm)
380= 380 mohm
045=45 mohm
1K5= 1.5ohm
M=Muti-EPI
R=Deep Trench

4. Vdss - Max（BVDSS / 10）
80= 800V VDS
65= 650V VDS

3. Channel /Type
C= Super junction

2. Package Code
K   TO-252-3L
L   SOT-23
G   PDFN5x6-8L / PDFN5x6-8L-D
Q   PDFN3.3x3.3-8L / PDFN3.3x3.3-8L-D
P   SOP-8
C   TO-220C-3L
E   TO-263-3L
J   SOT-23-3L

1. Prefix
CRM   CRM MOSFET

CRM MOSFET Naming Rule(SiC MOSFET/GaN HEMT)

1	2	3	4	5	6	7	
CRM	**K**	**S**	**80**	**P045**	**A**	**Q**	

7.Special Suffix
Default= Blank
Q= Automotive

6. Parameters option(use to distinguish part name when two devices have same process,package, Vds and Rdson range)

A= First 1
B= Option 2
K= with ESD(First1), KB with ESD(Option2)...
F= with FRD(First1), FB with FRD(Option2)...

5. CP Rds(on) Typ (mohm)
380= 380 mohm
045= 45 mohm
1K5= 1.5ohm
P= SiC
E= GaN E mode
D= GaN D mode

4. Vdss - Max（BVDSS / 10)
80= 800V VDS
65= 650V VDS

3. Channel /Type
S= SiC MOSFET
H= GaN HEMT

2. Package Code
K	TO-252-3L
L	SOT-23
G	PDFN5x6-8L / PDFN5x6-8L-D
Q	PDFN3.3x3.3-8L / PDFN3.3x3.3-8L-D
P	SOP-8
C	TO-220C-3L
E	TO-263-3L
J	SOT-23-3L

1. Prefix
CRM   CRM MOSFET

CRM MOSFET Naming Rule(Planar MOSFET)

1	2	3	4	5	6	7
CRM	K	P	4N	65	A	Q

7.Special Suffix
Default= Blank
Q= Automotive

6. Parameters option(use to distinguish part name when two devices have same process,package, Vds and Rdson range)
A= First 1
B= Option 2

5. Vdss - max
65=650V
100=1000V

4. ID - max
4N= 4A NMOS
10N= 10A NMOS
10P= 10A PMOS

3. Channel /Type
P= Planar MOSFET

2. Package Code
K   TO-252-3L
L   SOT-23
G   PDFN5x6-8L / PDFN5x6-8L-D
Q   PDFN3.3x3.3-8L / PDFN3.3x3.3-8L-D
P   SOP-8
C   TO-220C-3L
E   TO-263-3L
J   SOT-23-3L

1. Prefix
CRM   CRM MOSFET

CRM IGBT Discrete Naming Rule

1	2	3	4	5	6	7	8
CRT	**S**	**40**	**N**	**120**	**H**	**3**	**Q**

8.Default= Blank
Q= Automotive

7.Option
Generation

6. Frequency
RC= With FRED
H= High Frequency: up to 100Khz
M= Middle Frequency: up to 60Khz
L= Low Frequency: up to 20Khz

5. Voltage
95= 950V
120= 1200V

4. N/P Type
N= N type transistor
P= P type transistor

3. Current
40= 40A
400= 400A

2. Package Code
S= TO-247-3L
SA = TO-247-4L
E= TO-263-3L
C= TO-220C-3L
F= TO-220F-3L

1. Prefix
CRT   CRM IGBT Discrete

CRM IGBT Module Naming Rule

1	2	3	4	5	6	7	8	9
CRP	**40**	**R**	**120**	**BS**	**E3**	**HA**	**E**	**N**

Option

N= New Shell

Option

E= Enhancement(3DBC);blank=2DBC

7.IGBT Series
TA= Technology-SiC (Hybrid)
EA= Engine (Motor Control)
SA= Solar
HA= High frequency up to 100KHz
FA= Full speed ESS

6.Module Housing
62= 62 mm with Cu Base; HB2
A3= PPack3; HE3
B2/B3= EASY2/3 w/o Cu Base; HA2/HA3
C2/C3= ECP2/3; HF3(Flow2 with Cu Base)
D3= ED3 with Cu Base; HB3
E3= EASY3 with Cu Base;HF5
P2/P3= ECPIM2/3;HC2/HC3

5. Module Topology
P3= PIM Three Phase Input Rectifier
HB= Half Bridge
L3= 3 Level
P4= Four Pack
P6= Six Pack
PM= PIM
BS= Boost

4. Voltage
95= 950V
120= 1200V

3. Functionality
R= Reverse Conducting

2. Current
40= 40A
400= 400A

1. Prefix
CRP   CRM IGBT Module

Note: This excludes some part numbers commonly used in the industry, such as CRMLTL2N7002K, CRMLTU3400A, etc.